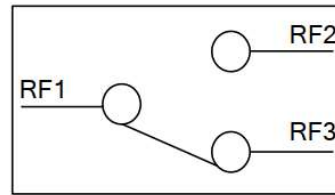


### Performance

- Frequency: 6-18GHz
- Insertion loss@0dBm: 1dB
- Insertion loss@38dBm: 1.5dB
- P-0.2:  $\geq 38$ dBm
- Isolation: 35dB
- Chip size: 1.3\*0.9\*0.08mm

### Function Diagram

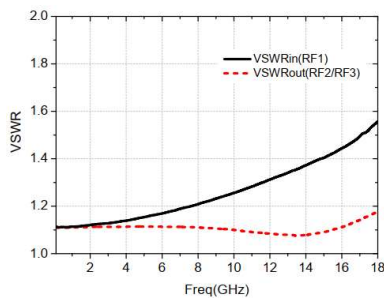


### Electrical Specifications (Ta=+25°C, Vc=0V/-20V, Pin=0dBm)

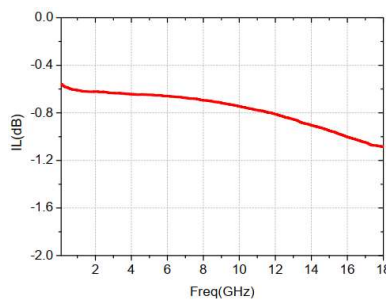
Parameter	Min	Typical	Max	Unit
Frequency Range	6-18			GHz
Insertion Loss@0dBm		1	1.2	dB
Insertion Loss@38dBm		1.5	2	dB
Isolation (ISO)	30	35		dB
Switch time (t)		15	30	ns
P-0.2	38			dBm
Input VSWR		1.4	1.6	-
Output VSWR		1.1	1.6	-

### Test Curves

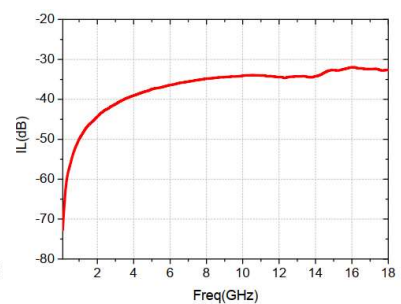
In/out VSWR vs. Freq



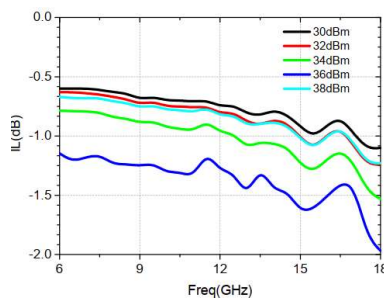
Insertion loss vs. Freq



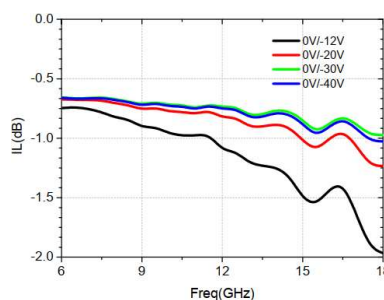
Isolation vs. Freq



Big signal IL vs. Freq (0V/-20V)



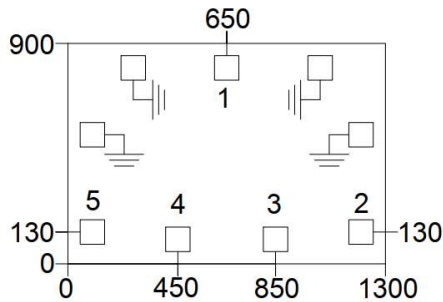
Big signal IL vs. Freq (34dBm)



### Truth Value

V1	V2	RF1- RF2	RF1- RF3
0	-20	OFF	ON
-20	0	ON	OFF

### Outline Size



### Note:

1. Unit:  $\mu\text{m}$
1. Bottom side is gold plated
2. Bottom side is GND
3. Bonding pads is gold plated
4. Don't bonding on thru holds
5. Tolerance:  $\pm 50\mu\text{m}$

### Pads Definition

No	Symbol	Description	Pad size
1	RF1	RF port, connect to $50\Omega$ system	$100*100\mu\text{m}$
5	RF2	RF port, connect to $50\Omega$ system	$100*100\mu\text{m}$
2	RF3	RF port, connect to $50\Omega$ system	$100*100\mu\text{m}$
4	V1	Bias voltage bonding pads	$100*100\mu\text{m}$
3	V2	Bias voltage bonding pads	$100*100\mu\text{m}$

### Absolute Max Ratings

Parameter	Symbol	Value
Negative supply	$V_c$	-50V
Max input power	$P_p$	+42dBm
Storage Temperature	$T_{STG}$	-65 ~ +150°C
Operating Temperature	$T_{op}$	-55 ~ +125°C

### Assembly

